

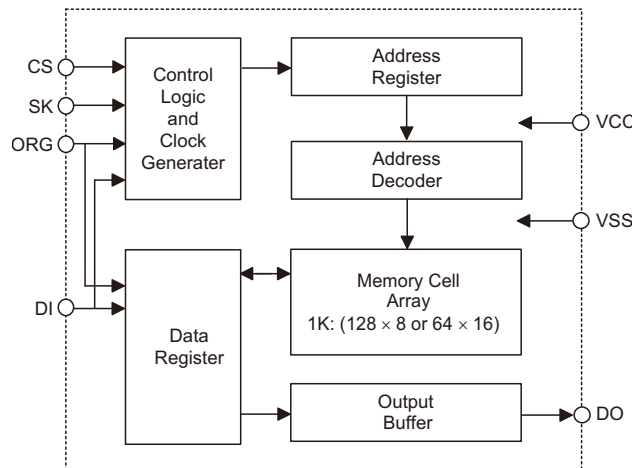
Features

- Operating voltage: 1.8V~5.5V
- Low power consumption
 - Operating: 5mA max.
 - Standby: 2μA max.
- User selectable internal organization
 - 1K: 128×8 or 64×16
- 3-wire Serial Interface
- Write cycle time: 5ms max.
- Automatic erase-before-write operation
- Word/chip erase and write operation
- Write operation with built-in timer
- Software controlled write protection
- 40-year data retention
- 10⁶ rewrite cycles per word
- Industrial temperature range (−40°C to +85°C)
- 8-pin DIP/SOP/TSSOP package

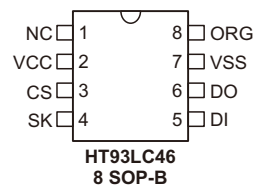
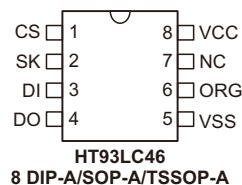
General Description

The HT93LC46 is a 1K-bit low voltage nonvolatile, serial electrically erasable programmable read only memory device using the CMOS floating gate process. Its 1024 bits of memory are organized into 64 words of 16 bits each when the ORG pin is connected to VCC or organized into 128 words of 8 bits each when it is tied to VSS. The device is optimized for use in many industrial and commercial applications where low power and low voltage operation are essential. By popular microcontroller, the versatile serial interface including chip select (CS), serial clock (SK), data input (DI) and data output (DO) can be easily controlled.

Block Diagram



Pin Assignment



Pin Description

Pin Name	I/O	Description
CS	I	Chip select input
SK	I	Serial clock input
DI	I	Serial data input
DO	O	Serial data output
VSS	—	Negative power supply, ground
ORG	I	Internal Organization When ORG is connected to VDD or ORG is floated, the (×16) memory organization is selected. When ORG is tied to VSS, the (×8) memory organization is selected. There is an internal pull-up resistor on the ORG pin.
NC	—	No connection
VCC	—	Positive power supply

Absolute Maximum Ratings

Supply Voltage	$V_{SS}-0.3V$ to $V_{SS}+6.0V$	Storage Temperature	$-50^{\circ}C$ to $125^{\circ}C$
Input Voltage	$V_{SS}-0.3V$ to $V_{CC}+0.3V$	Operating Temperature	$-40^{\circ}C$ to $85^{\circ}C$

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

D.C. Characteristics

$T_a = -40^{\circ}C \sim +85^{\circ}C$

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
		V_{CC}	Conditions				
V_{CC}	Operating Voltage	—	$-40^{\circ}C$ to $+85^{\circ}C$	1.8	—	5.5	V
I_{CC1}	Operating Current (TTL)	5V	DO unload, SK=1MHz	—	—	5	mA
I_{CC2}	Operating Current (CMOS)	5V	DO unload, SK=1MHz	—	—	5	mA
		1.8V~5.5V	DO unload, SK=250kHz	—	—	5	mA
I_{STB}	Standby Current (CMOS)	1.8V~5.5V	CS=SK=DI=0V	—	—	2	μA
I_{LI}	Input Leakage Current	5V	$V_{IN}=V_{SS}-V_{CC}$	0	—	1	μA
I_{LO}	Output Leakage Current	5V	$V_{OUT}=V_{SS}-V_{CC}$, CS=0V	0	—	1	μA
V_{IL}	Input Low Voltage	5V	—	0	—	0.8	V
		1.8V~5.5V	—	0	—	$0.1V_{CC}$	V
V_{IH}	Input High Voltage	5V	—	2	—	V_{CC}	V
		1.8V~5.5V	—	$0.9V_{CC}$	—	V_{CC}	V
V_{OL}	Output Low Voltage	5V	$I_{OL}=2.1mA$	—	—	0.4	V
		1.8V~5.5V	$I_{OL}=100\mu A$	—	—	0.2	V
V_{OH}	Output High Voltage	5V	$I_{OH}=-400\mu A$	2.4	—	—	V
		1.8V~5.5V	$I_{OH}=-100\mu A$	$V_{CC}-0.2$	—	—	V
C_{IN}	Input Capacitance (see note)	—	$V_{IN}=0V$, $f=250kHz$	—	—	5	pF
C_{OUT}	Output Capacitance (see note)	—	$V_{OUT}=0V$, $f=250kHz$	—	—	5	pF

Note: These parameters are periodically sampled but not 100% tested.

A.C. Characteristics

 $T_a = -40^{\circ}\text{C} \sim +85^{\circ}\text{C}$

Symbol	Parameter	$V_{CC}=5V \pm 10\%$		$V_{CC}=3V \pm 10\%$		$V_{CC}=1.8V$		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
f_{SK}	Clock Frequency	0	2000	0	1000	0	500	kHz
t_{SKH}	SK High Time	250	—	500	—	1000	—	ns
t_{SKL}	SK Low Time	250	—	500	—	1000	—	ns
t_{CSS}	CS Setup Time	50	—	100	—	100	—	ns
t_{CSH}	CS Hold Time	0	—	0	—	0	—	ns
t_{CDS}	CS Deselect Time	250	—	250	—	500	—	ns
t_{DIS}	DI Setup Time	100	—	150	—	200	—	ns
t_{DIH}	DI Hold Time	100	—	150	—	200	—	ns
t_{PD1}	DO Delay to "1"	—	250	—	500	—	1000	ns
t_{PD0}	DO Delay to "0"	—	250	—	500	—	1000	ns
t_{SV}	Status Valid Time	—	250	—	250	—	250	ns
t_{HZ}	DO Disable Time	—	100	—	200	—	400	ns
t_{PR}	Write Cycle Time	—	5	—	5	—	5	ms
Endurance	25°C, Page Mode, 5.0V	1,000,000						Write Cycles

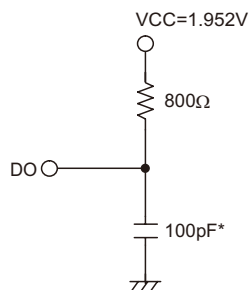
Note: These parameters are periodically sampled but not 100% tested.
For relative timing, refer to timing diagrams.

A.C. Test Conditions

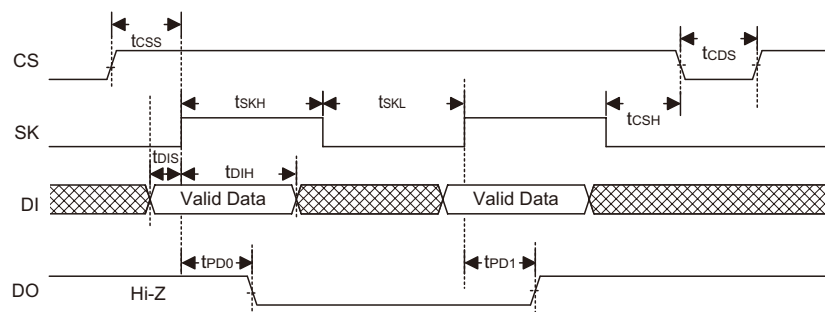
Input rise and fall time: 5ns (1V to 2V)

Input and output timing reference levels: 1.5V

Output load: See Figure right



*Including scope and jig
Output Load Circuit



Functional Description

The HT93LC46 is accessed via a three-wire serial communication interface. The device is arranged into 64 words by 16 bits or 128 words by 8 bits depending whether the ORG pin is connected to VCC or VSS. The HT93LC46 contains seven instructions: READ, ERASE, WRITE, EWEN, EWDS, ERAL and WRAL. When the user selectable internal organization is arranged into 64×16 (128×8), these instructions are all made up of 9(10) bits data: 1 start bit, 2 op code bits and 6(7) address bits.

By using the control signal CS, SK and data input signal DI, these instructions can be given to the HT93LC46. These serial instruction data presented at the DI input will be written into the device at the rising edge of SK. During the READ cycle, DO pin acts as the data output and during the WRITE or ERASE cycle, DO pin indicates the BUSY/READY status. When the DO pin is active for read data or as a BUSY/READY indicator the CS pin must be high; otherwise DO pin will be in a high-impedance state. For successful instructions, CS must be low once after the instruction is sent. After power on, the device is by default in the EWDS state. And, an EWEN instruction must be performed before any ERASE or WRITE instruction can be executed. The following are the functional descriptions and timing diagrams of all seven instructions.

READ

The READ instruction will stream out data at a specified address on the DO pin. The data on DO pin changes during the low-to-high edge of SK signal. The 8 bits or 16 bits data stream is preceded by a logical "0" dummy bit. Irrespective of the condition of the EWEN or EWDS instruction, the READ command is always valid and independent of these two instructions. After the data word has been read the internal address will be automatically incremented by 1 allowing the next consecutive data word to be read out without entering further address data. The address will wrap around with CS High until CS returns to LOW.

EWEN/EWDS

The EWEN/EWDS instruction will enable or disable the programming capabilities. At both the power on and power off state the device automatically entered the disable mode. Before a WRITE, ERASE, WRAL or ERAL instruction is given, the programming enable instruction EWEN must be issued, otherwise the ERASE/WRITE instruction is invalid. After the EWEN instruction is issued, the programming enable condition remains until power is turned off or a EWDS instruction is given. No data can be written into the device in the programming disabled state. By so doing, the internal memory data can be protected.

ERASE

The ERASE instruction erases data at the specified addresses in the programming enable mode. After the ERASE op-code and the specified address have been issued, the data erase is activated by the falling edge of CS. Since the internal auto-timing generator provides all timing signals for the internal erase, so the SK clock is not required. During the internal erase, we can verify the busy/ready status if CS is high. The DO pin will remain low but when the operation is over, the DO pin will return to high and further instructions can be executed.

WRITE

The WRITE instruction writes data into the device at the specified addresses in the programming enable mode. After the WRITE op-code and the specified address and data have been issued, the data writing is activated by the falling edge of CS. Since the internal auto-timing generator provides all timing signal for the internal writing, so the SK clock is not required. The auto-timing write cycle includes an automatic erase-before-write capability. So, it is not necessary to erase data before the WRITE instruction. During the internal writing, we can verify the busy/ready status if CS is high. The DO pin will remain low but when the operation is over, the DO pin will return to high and further instructions can be executed.

ERAL

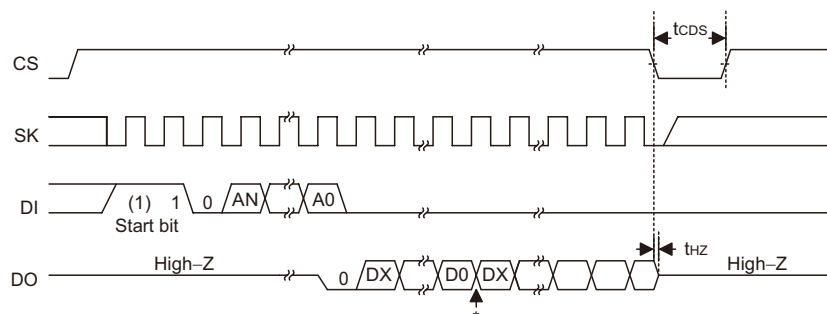
The ERAL instruction erases the entire 64×16 or 128×8 memory cells to logical "1" state in the programming enable mode. After the erase-all instruction set has been issued, the data erase feature is activated by the falling edge of CS. Since the internal auto-timing generator provides all timing signal for the erase-all operation, so the SK clock is not required. During the internal erase-all operation, we can verify the busy/ready status if CS is high. The DO pin will remain low but when the operation is over, the DO pin will return to high and further instruction can be executed.

WRAL

The WRAL instruction writes data into the entire 64×16 or 128×8 memory cells in the programming enable mode. After the write-all instruction set has been issued, the data writing is activated by the falling edge of CS. Since the internal auto-timing generator provides all timing signals for the write-all operation, so the SK clock is not required. During the internal write-all operation, we can verify the busy/ready status if CS is high. The DO pin will remain low but when the operation is over the DO pin will return to high and further instruction can be executed.

Timing Diagrams

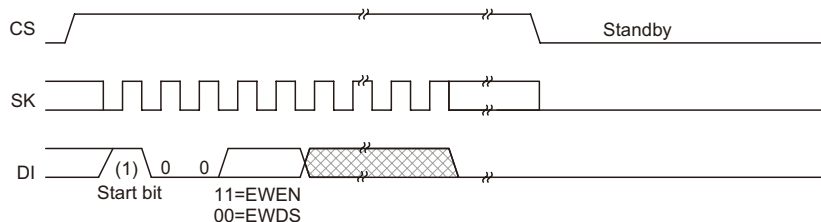
READ



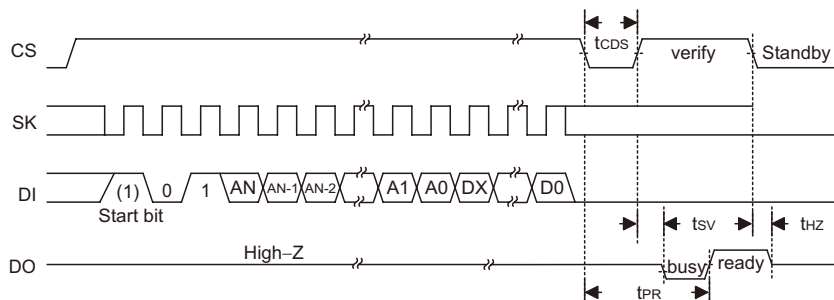
* Address pointer automatically cycles to the next word

Mode	(X16)	(X8)
AN	A5	A6
DX	D15	D7

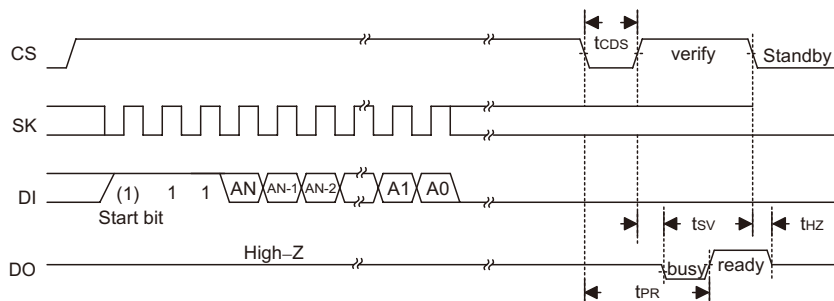
EWEN/EWDS

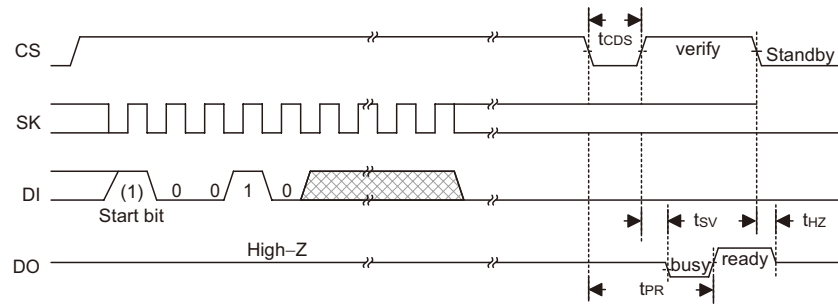
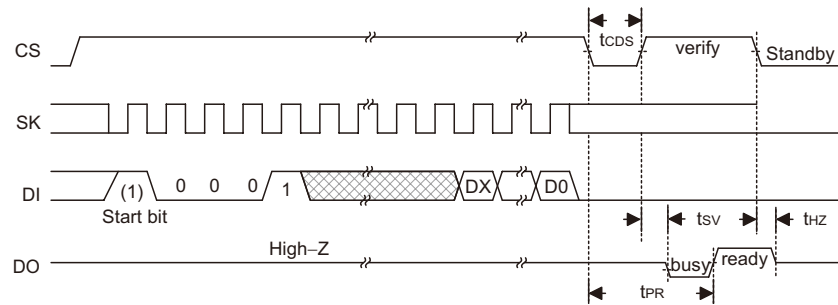


WRITE



ERASE



ERAL

WRAL

Instruction Set Summary

Instruction	Comments	Start Bit	Op Code	Address		Data	
				ORG=0 ×8	ORG=1 ×16	ORG=0 ×8	ORG=1 ×16
READ	Read data	1	10	A6~A0	A5~A0	D7~D0	D15~D0
ERASE	Erase data	1	11	A6~A0	A5~A0	—	
WRITE	Write data	1	01	A6~A0	A5~A0	D7~D0	D15~D0
EWEN	Erase/Write Enable	1	00	11XXXXXX	11XXXXXX	—	
EWDS	Erase/Write Disable	1	00	00XXXXXX	00XXXXXX	—	
ERAL	Erase All	1	00	10XXXXXX	10XXXXXX	—	
WRAL	Write All	1	00	01XXXXXX	01XXXXXX	D7~D0	D15~D0

Note: "X" stands for "don't care"

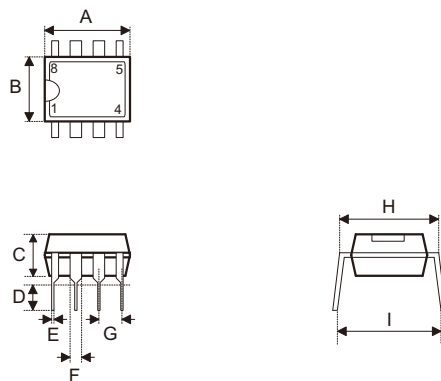
Data should be written to the EEPROM in the format (8-bit or 16-bit mode) in which it is to be read.

Package Information

Note that the package information provided here is for consultation purposes only. As this information may be updated at regular intervals users are reminded to consult the [Holtek website](#) for the latest version of the package information.

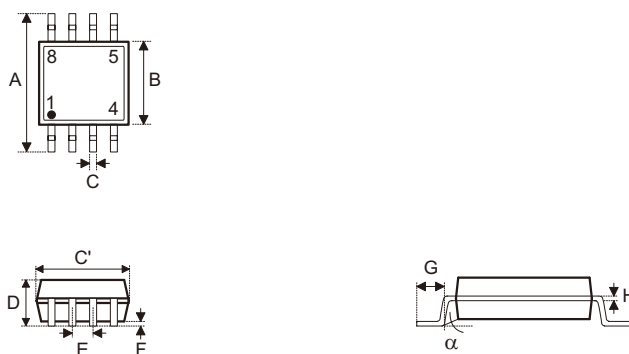
Additional supplementary information with regard to packaging is listed below. Click on the relevant section to be transferred to the relevant website page.

- [Further Package Information](#) (include Outline Dimensions, Product Tape and Reel Specifications)
- [Packing Materials Information](#)
- [Carton information](#)

8-pin DIP (300mil) Outline Dimensions


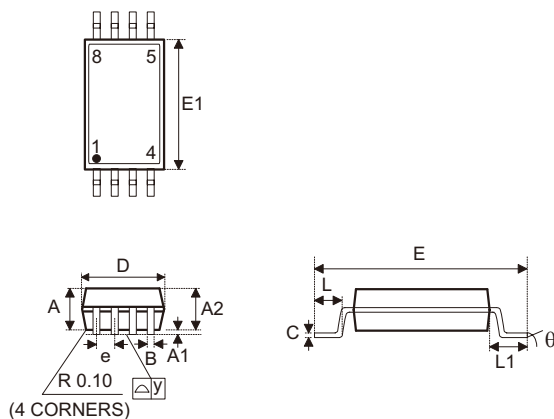
Symbol	Dimensions in inch		
	Min.	Nom.	Max.
A	0.355	0.365	0.400
B	0.240	0.250	0.280
C	0.115	0.130	0.195
D	0.115	0.130	0.150
E	0.014	0.018	0.022
F	0.045	0.060	0.070
G	—	0.100 BSC	—
H	0.300	0.310	0.325
I	—	—	0.430

Symbol	Dimensions in mm		
	Min.	Nom.	Max.
A	9.02	9.27	10.16
B	6.10	6.35	7.11
C	2.92	3.30	4.95
D	2.92	3.30	3.81
E	0.36	0.46	0.56
F	1.14	1.52	1.78
G	—	2.54 BSC	—
H	7.26	7.87	8.26
I	—	—	10.92

8-pin SOP (150mil) Outline Dimensions


Symbol	Dimensions in inch		
	Min.	Nom.	Max.
A	—	0.236 BSC	—
B	—	0.154 BSC	—
C	0.012	—	0.020
C'	—	0.193 BSC	—
D	—	—	0.069
E	—	0.050 BSC	—
F	0.004	—	0.010
G	0.016	—	0.050
H	0.004	—	0.010
α	0°	—	8°

Symbol	Dimensions in mm		
	Min.	Nom.	Max.
A	—	6.00 BSC	—
B	—	3.90 BSC	—
C	0.31	—	0.51
C'	—	4.90 BSC	—
D	—	—	1.75
E	—	1.27 BSC	—
F	0.10	—	0.25
G	0.40	—	1.27
H	0.10	—	0.25
α	0°	—	8°

8-pin TSSOP Outline Dimensions


Symbol	Dimensions in inch		
	Min.	Nom.	Max.
A	—	—	0.047
A1	0.002	—	0.006
A2	0.031	0.039	0.041
B	0.007	—	0.012
C	0.004	—	0.006
D	0.114	0.118	0.122
E	—	0.252 BSC	—
E1	0.169	0.173	0.177
e	—	0.026 BSC	—
L	0.018	0.024	0.030
L1	—	0.039 BSC	—
y	—	0.004	—
θ	0°	—	8°

Symbol	Dimensions in mm		
	Min.	Nom.	Max.
A	—	—	1.20
A1	0.05	—	0.15
A2	0.80	1	1.05
B	0.19	—	0.30
C	0.09	—	0.16
D	2.90	3.00	3.10
E	—	6.40 BSC	—
E1	4.30	4.40	4.50
e	—	0.65 BSC	—
L	0.45	0.60	0.75
L1	—	1.0 BSC	—
y	—	0.10	—
θ	0°	—	8°

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